

100V N-CHANNEL MOSFET IN DFN5060 PACKAGE



Features

- Split Gate Trench (SGT) Power MOSFET Technology for enhanced efficiency
- Low $R_{DS(on)}$ of 5.2m Ω for reduced conduction losses
- Low gate charge for fast switching and low drive requirements
- Compact DFN5060 package with an optimized footprint of 5.0mm x 6.0mm
- Low thermal resistance for improved heat dissipation and reliability



Benefits

Low $R_{DS(on)}$ and gate charge minimize power losses, helping to maximize system efficiency.

Reduced gate charge enables quicker switching speeds, supporting high-frequency designs and reducing overall system response time.

Applications



Power supply
units



Relay
replacements



Lighting
control

Enhance Your Designs with MCC's MCAC5D2N10Y-TP 100V N-Channel MOSFET



**The DFN5060 package
combines superior
thermal performance
w/ space-saving design**

Utilizes advanced Split Gate Trench (SGT) technology to offer an ultra low RDS(on) of 5.2mΩ



Product Attributes, Parametrics & Datasheets

Product	Type	Package	Drain Source Voltage VDS	Drain Source On-Resistance (max.) RDS(on)	Continuous Drain Current ID	Total Power Dissipation PD	Mounting Type	Datasheet
MCAC5D2N10Y	Power MOSFET	DFN5060	100V	117V	117A	138W	Surface Mount	Info

Applications:



Power Management

- Battery management systems
- DC-DC converters
- Power supply units



Industrial Automation

- Motor drivers
- Relay replacements
- Solenoid drivers



Lighting

- LED lighting control
- Electronic ballasts



Consumer Electronics

- Battery management systems
- Lighting control
- Motor drivers

CONTACT MCC TO REQUEST A SAMPLE

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